

MUN5130DW1, NSBA113EDXV6

Dual PNP Bias Resistor Transistors

R1 = 1 kΩ, R2 = 1 kΩ

PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

(T_A = 25°C, common for Q1 and Q2, unless otherwise noted)

| Rating | Symbol | Max | Unit |
|--------------------------------|----------------------|-----|------|
| Collector-Base Voltage | V _{CBO} | 50 | Vdc |
| Collector-Emitter Voltage | V _{CEO} | 50 | Vdc |
| Collector Current – Continuous | I _C | 100 | mAdc |
| Input Forward Voltage | V _{IN(fwd)} | 10 | Vdc |
| Input Reverse Voltage | V _{IN(rev)} | 10 | Vdc |

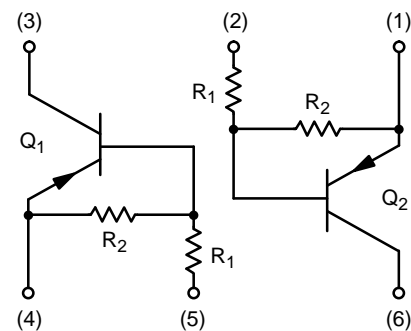
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



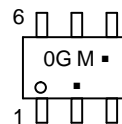
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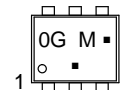
PIN CONNECTIONS



MARKING DIAGRAMS



SOT-363
CASE 419B



SOT-563
CASE 463A

0G = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping† |
|-----------------|----------------------|--------------------|
| MUN5130DW1T1G | SOT-363 (Pb-Free) | 3000 / Tape & Reel |
| NSBA113EDXV6T1G | SOT-563 (Pb-Free) | 4000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MUN5130DW1, NSBA113EDXV6

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|----------------|--------|-----|------|
|----------------|--------|-----|------|

MUN5130DW1 (SOT-363) One Junction Heated

| | | | |
|---|-----------------|--------------------------|----------------------------|
| Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1) (Note 2) Derate above 25°C (Note 1) (Note 2) | P_D | 187 256 1.5 2.0 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction to Ambient (Note 1) (Note 2) | $R_{\theta JA}$ | 670 490 | $^\circ\text{C}/\text{W}$ |

MUN5130DW1 (SOT-363) Both Junction Heated (Note 3)

| | | | |
|---|-----------------|--------------------------|----------------------------|
| Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1) (Note 2) Derate above 25°C (Note 1) (Note 2) | P_D | 250 385 2.0 3.0 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction to Ambient (Note 1) (Note 2) | $R_{\theta JA}$ | 493 325 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction to Lead (Note 1) (Note 2) | $R_{\theta JL}$ | 188 208 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

NSBA113EDXV6 (SOT-563) One Junction Heated

| | | | |
|---|-----------------|------------|----------------------------|
| Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1) Derate above 25°C (Note 1) | P_D | 357 2.9 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction to Ambient (Note 1) | $R_{\theta JA}$ | 350 | $^\circ\text{C}/\text{W}$ |

NSBA113EDXV6 (SOT-563) Both Junction Heated (Note 3)

| | | | |
|---|-----------------|-------------|----------------------------|
| Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1) Derate above 25°C (Note 1) | P_D | 500 4.0 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction to Ambient (Note 1) | $R_{\theta JA}$ | 250 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- Both junction heated values assume total power is sum of two equally powered channels.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, common for Q_1 and Q_2 , unless otherwise noted)

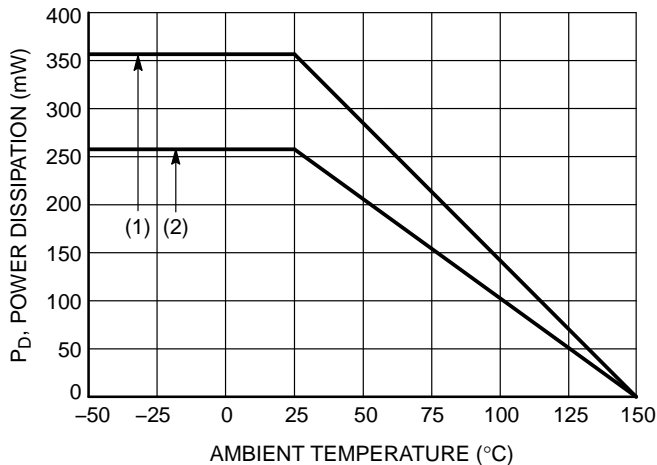
| Characteristic | Symbol | Min | Typ | Max | Unit |
|---|---------------|-----|-----|-----|------|
| OFF CHARACTERISTICS | | | | | |
| Collector–Base Cutoff Current ($V_{CB} = 50\text{ V}$, $I_E = 0$) | I_{CBO} | – | – | 100 | nAdc |
| Collector–Emitter Cutoff Current ($V_{CE} = 50\text{ V}$, $I_B = 0$) | I_{CEO} | – | – | 500 | nAdc |
| Emitter–Base Cutoff Current ($V_{EB} = 6.0\text{ V}$, $I_C = 0$) | I_{EBO} | – | – | 4.3 | mAdc |
| Collector–Base Breakdown Voltage ($I_C = 10\ \mu\text{A}$, $I_E = 0$) | $V_{(BR)CBO}$ | 50 | – | – | Vdc |
| Collector–Emitter Breakdown Voltage (Note 4) ($I_C = 2.0\text{ mA}$, $I_B = 0$) | $V_{(BR)CEO}$ | 50 | – | – | Vdc |

ON CHARACTERISTICS

| | | | | | |
|--|---------------|-----|-----|------|------------------|
| DC Current Gain (Note 4) ($I_C = 5.0\text{ mA}$, $V_{CE} = 10\text{ V}$) | h_{FE} | 3.0 | 5.0 | – | |
| Collector–Emitter Saturation Voltage (Note 4) ($I_C = 10\text{ mA}$, $I_B = 5.0\text{ mA}$) | $V_{CE(sat)}$ | – | – | 0.25 | Vdc |
| Input Voltage (off) ($V_{CE} = 5.0\text{ V}$, $I_C = 100\ \mu\text{A}$) | $V_{i(off)}$ | – | 1.3 | – | Vdc |
| Input Voltage (on) ($V_{CE} = 0.2\text{ V}$, $I_C = 20\text{ mA}$) | $V_{i(on)}$ | – | 1.7 | – | Vdc |
| Output Voltage (on) ($V_{CC} = 5.0\text{ V}$, $V_B = 2.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$) | V_{OL} | – | – | 0.2 | Vdc |
| Output Voltage (off) ($V_{CC} = 5.0\text{ V}$, $V_B = 0.05\text{ V}$, $R_L = 1.0\text{ k}\Omega$) | V_{OH} | 4.9 | – | – | Vdc |
| Input Resistor | R_1 | 0.7 | 1.0 | 1.3 | $\text{k}\Omega$ |
| Resistor Ratio | R_1/R_2 | 0.8 | 1.0 | 1.2 | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle $\leq 2\%$.



- (1) SOT-363; 1.0 x 1.0 inch Pad
- (2) SOT-563; Minimum Pad

Figure 1. Derating Curve

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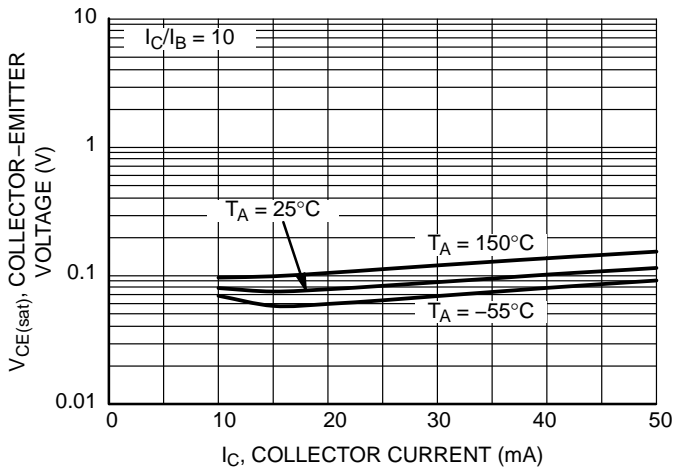


Figure 2. $V_{CE(sat)}$ vs. I_C

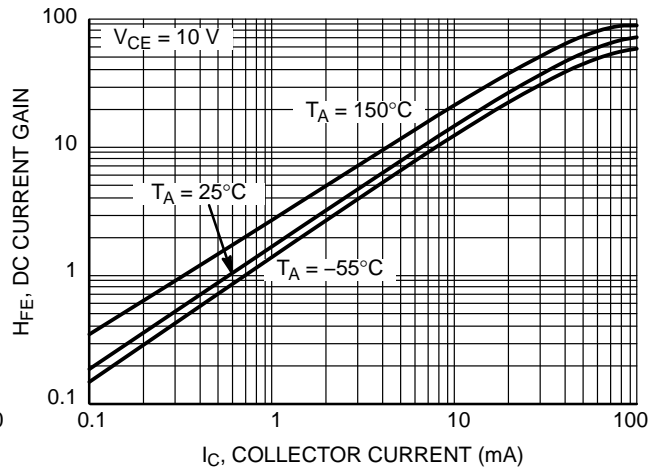


Figure 3. DC Current Gain

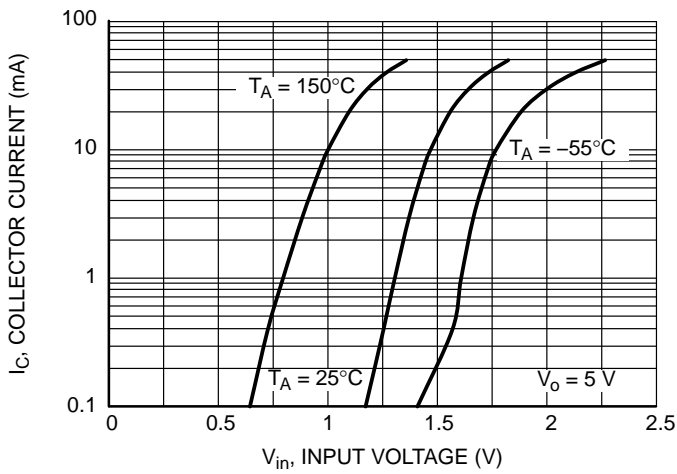


Figure 4. Output Current vs. Input Voltage

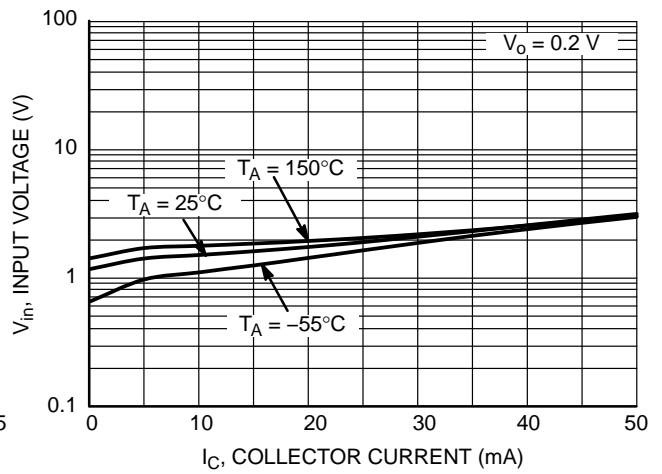


Figure 5. Input Voltage vs. Output Current

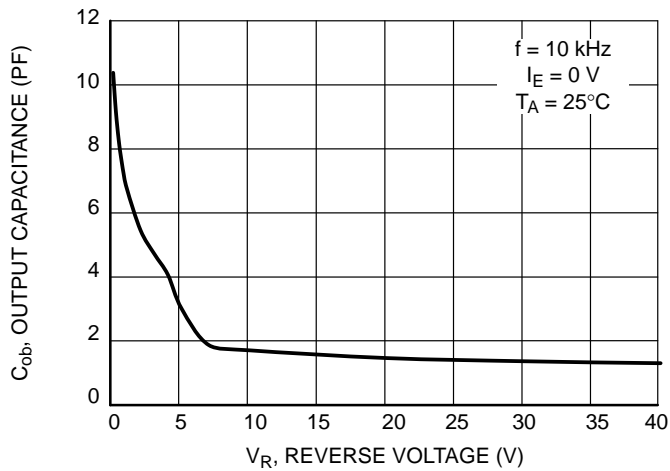
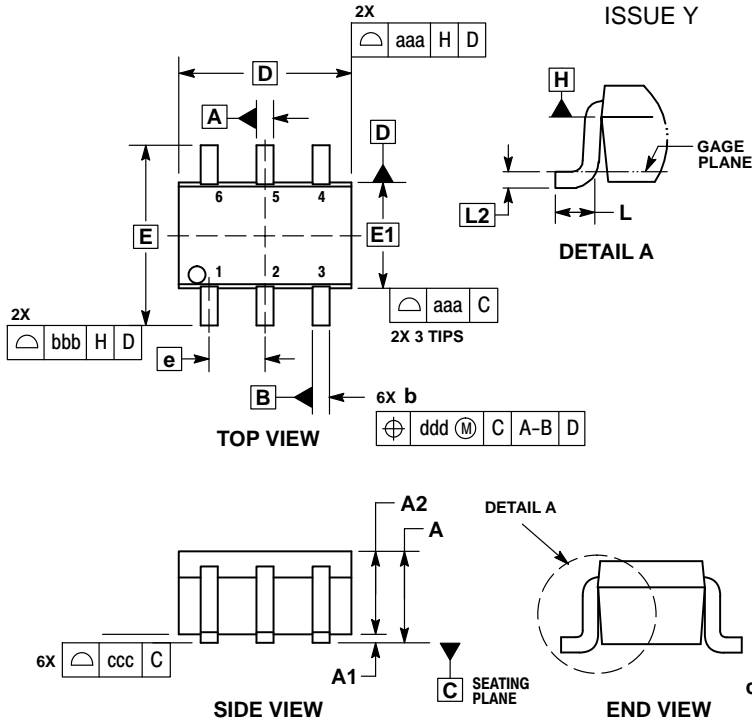


Figure 6. Output Capacitance

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PACKAGE DIMENSIONS

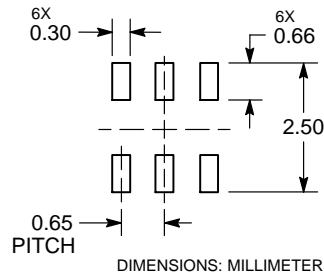
SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE Y



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 5. DATUMS A AND B ARE DETERMINED AT DATUM H.
 6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|-----------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | --- | --- | 1.10 | --- | --- | 0.043 |
| A1 | 0.00 | --- | 0.10 | 0.000 | --- | 0.004 |
| A2 | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| C | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |
| E | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |
| E1 | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 0.65 BSC | | | 0.026 BSC | | |
| L | 0.26 | 0.36 | 0.46 | 0.010 | 0.014 | 0.018 |
| L2 | 0.15 BSC | | | 0.006 BSC | | |
| aaa | 0.15 | | | 0.006 | | |
| bbb | 0.30 | | | 0.012 | | |
| ccc | 0.10 | | | 0.004 | | |
| ddd | 0.10 | | | 0.004 | | |

RECOMMENDED SOLDERING FOOTPRINT*

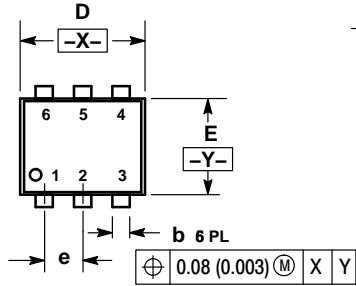


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A ISSUE G

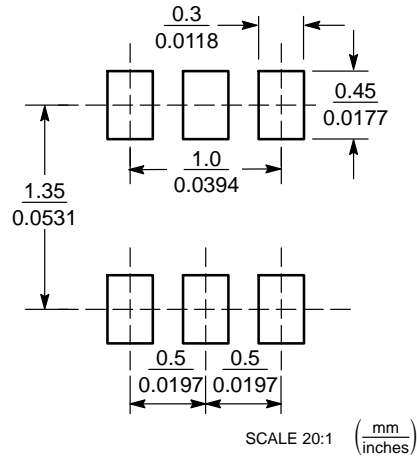


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|----------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.50 | 0.55 | 0.60 | 0.020 | 0.021 | 0.023 |
| b | 0.17 | 0.22 | 0.27 | 0.007 | 0.009 | 0.011 |
| C | 0.08 | 0.12 | 0.18 | 0.003 | 0.005 | 0.007 |
| D | 1.50 | 1.60 | 1.70 | 0.059 | 0.062 | 0.066 |
| E | 1.10 | 1.20 | 1.30 | 0.043 | 0.047 | 0.051 |
| e | 0.5 BSC | | | 0.02 BSC | | |
| L | 0.10 | 0.20 | 0.30 | 0.004 | 0.008 | 0.012 |
| HE | 1.50 | 1.60 | 1.70 | 0.059 | 0.062 | 0.066 |

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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